

# **Isc N-Channel MOSFET Transistor**

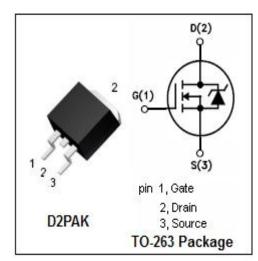
## IPB60R199CP

### • FEATURES

- · With To-263(D2PAK) package
- · Low input capacitance and gate charge
- · Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



Switching applications

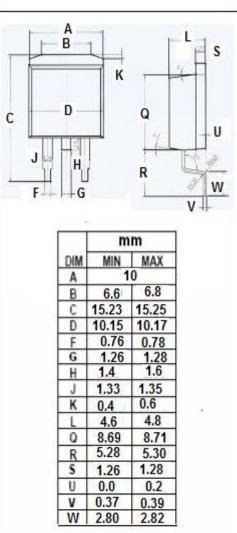


• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                                 | VALUE    | UNIT                 |
|------------------|---|----------|----------------------|
| V <sub>DSS</sub> | Drain-Source Voltage                      | 600      | V                    |
| V <sub>GSS</sub> | Gate-Source Voltage                       | ±30      | V                    |
| I <sub>D</sub>   | Drain Current-ContinuousTc=25℃<br>Tc=100℃ | 16<br>10 | А                    |
| I <sub>DM</sub>  | Drain Current-Single Pulsed               | 51       | А                    |
| P <sub>D</sub>   | Total Dissipation @Tc=25℃                 | 139      | W                    |
| T <sub>ch</sub>  | Max. Operating Junction Temperature       | 150      | $^{\circ}\mathbb{C}$ |
| T <sub>stg</sub> | Storage Temperature                       | -55~150  | $^{\circ}$ C         |

## • THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                             |     | UNIT |  |
|-----------|---------------------------------------|-----|------|--|
| Rth(ch-c) | Channel-to-case thermal resistance    | 0.9 | °C/W |  |
| Rth(ch-a) | Channel-to-ambient thermal resistance |     | °C/W |  |



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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS  | MIN | ТҮР | MAX      | UNIT |
|---------------------|--------------------------------|---|-----|-----|----------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> =0.25mA   | 600 |     |          | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =1.1mA  | 2.5 |     | 3.5      | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =9.9A   |     | 180 | 199      | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V  |     |     | ±0.1     | μА   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V;Tj=25°C<br>V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V;Tj=150°C |     |     | 1<br>100 | μА   |
| V <sub>SDF</sub>    | Diode forward voltage          | I <sub>SD</sub> =9.9A, V <sub>GS</sub> = 0 V  |     | 0.9 | 1.2      | V    |

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